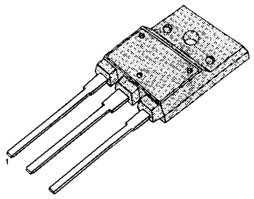
KSC5086

NPN TRIPLE DIFFUSED PLANAR SILICON TRANSISTOR

HIGH DEFINITION COLOR DISPLAY HORIZONTAL DEFLECTION OUTPUT (DAMPER DIODE BUILT IN)

- High Collector -Base Voltage (V_{CBO}=1500V)
- High Speed Switching (tf=0.1usec Typ)

TO-3PF



1. Base 2. Collector 3. Emitter

ABSOLUTE MIXIMUM RATING

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V_{CBO}	1500	V
Collector Emitter Voltage	V_{CEO}	800	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current (DC)	I_C	7	A
Collector Current (Pulse)	I_C	16	A
Collector Dissipation (T_C=25℃)	P_C	50	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55 ~ 150	℃

ELECTRICAL CHARACTERISTICS (T_C=25℃)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current (V_{BE}=0)	I_{CES}	V_{CE} = 1400V, R_{BE} = 0			1	mA
Collector Cutoff Current	I_{CBO}	V_{CB}=800V, I_E=0			10	uA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 4V, I_C = 0	40		200	mA
Base Emitter Breakdown Voltage	V_{EBO}	I_E = 250mA, I_C = 0	6			V
DC Current Gain	h_{FE}	V_{CE} = 5V, I_C = 1.0A	8			
Collector Emitter Saturation Voltage	V_{CE}(sat)	I_C = 5A, I_B = 1.2A			5	V
Base Emitter Saturation Voltage	V_{BE}(sat)	I_C = 5A, I_B = 1.2A			1.5	V
Damper Diode Turn On Voltage	V_F	I_F= 6A			2	V
Fall Time	t_F	V_{CC} = 200V, I_C = 4A I_B1 = 0.8A, I_B2 = -1.6A RL = 50Ω			0.2	uS